

# TYPES 2N2483, 2N2484 N-P-N SILICON TRANSISTORS

BULLETIN NO. DL-S 6710300, SEPTEMBER 1967

## FOR LOW-LEVEL, LOW-NOISE, HIGH-GAIN, AMPLIFIER APPLICATIONS

- Guaranteed Low-Noise Characteristics at 100 Hz, 1 kHz, and 10 kHz
- High  $V_{(BR)CEO} \dots 60$  V Min
- D-C Beta Guaranteed at  $I_C = 1 \mu A$  (2N2484)

### \*mechanical data



### \*absolute maximum ratings at 25°C free-air temperature (unless otherwise noted)

Collector-Base Voltage	60 V
Collector-Emitter Voltage (See Note 1)	60 V
Emitter-Base Voltage	6 V
Continuous Collector Current	50 mA
Continuous Device Dissipation at (or below) 25°C Free-Air Temperature (See Note 2)	0.36 W
Continuous Device Dissipation at (or below) 25°C Case Temperature (See Note 3)	1.2 W
Continuous Device Dissipation at 100°C Case Temperature	0.68 W
Storage Temperature Range	-65°C to 200°C
Lead Temperature $\frac{1}{16}$ Inch from Case for 10 Seconds	300°C

- NOTES: 1. This value applies when the base-emitter diode is open-circuited.  
 2. Derate linearly to 200°C free-air temperature at the rate of 2.06 mW/deg.  
 3. Derate linearly to 200°C case temperature at the rate of 6.65 mW/deg.

\*Indicates JEDEC registered data

USES CHIP N11

# TYPES 2N2483, 2N2484

## N-P-N SILICON TRANSISTORS

\*electrical characteristics at 25°C free-air temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS	2N2483		2N2484		UNIT
		MIN	MAX	MIN	MAX	
$V_{(BR)CBO}$ Collector-Base Breakdown Voltage	$I_C = 10 \mu A, I_E = 0$	60		60		V
$V_{(BR)CEO}$ Collector-Emitter Breakdown Voltage	$I_C = 10 mA, I_B = 0$ , See Note 4	60		60		V
$V_{(BR)EBO}$ Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	6		6		V
$I_{CBO}$ Collector Cutoff Current	$V_{CB} = 45 V, I_E = 0$		10		10	nA
$I_{EBO}$ Emitter Cutoff Current	$V_{EB} = 5 V, I_C = 0$		10		10	nA
$h_{FE}$ Static Forward Current Transfer Ratio	$V_{CE} = 5 V, I_C = 1 \mu A$			30		
	$V_{CE} = 5 V, I_C = 10 \mu A$	40	120	100	500	
	$V_{CE} = 5 V, I_C = 10 \mu A, T_A = -55^\circ C$	10		20		
	$V_{CE} = 5 V, I_C = 100 \mu A$	75		175		
	$V_{CE} = 5 V, I_C = 500 \mu A$	100		200		
	$V_{CE} = 5 V, I_C = 1 mA$	175		250		
$V_{BE}$ Base-Emitter Voltage	$V_{CE} = 5 V, I_C = 100 \mu A$	0.5	0.7	0.5	0.7	V
$V_{CE(sat)}$ Collector-Emitter Saturation Voltage	$I_B = 100 \mu A, I_C = 1 mA$		0.35		0.35	V
$h_{ie}$ Small-Signal Common-Emitter Input Impedance	$V_{CE} = 5 V, I_C = 1 mA, f = 1 kHz$	1.5	13	3.5	24	k $\Omega$
$h_{fe}$ Small-Signal Common-Emitter Forward Current Transfer Ratio		80	450	150	900	
$h_{re}$ Small-Signal Common-Emitter Reverse Voltage Transfer Ratio			$8 \times 10^{-4}$		$8 \times 10^{-4}$	
$h_{oe}$ Small-Signal Common-Emitter Output Admittance			30		40	$\mu mho$
$ h_{fe} $ Small-Signal Common-Emitter Forward Current Transfer Ratio	$V_{CE} = 5 V, I_C = 50 \mu A, f = 5 MHz$	2.4		3		
	$V_{CE} = 5 V, I_C = 500 \mu A, f = 30 MHz$	2		2		
$C_{obo}$ Common-Base Open-Circuit Output Capacitance	$V_{CB} = 5 V, I_E = 0, f = 140 kHz$		6		6	pF
$C_{ibo}$ Common-Base Open-Circuit Input Capacitance	$V_{EB} = 0.5 V, I_C = 0, f = 140 kHz$		6		6	pF

\*operating characteristics at 25°C free-air temperature

PARAMETER	TEST CONDITIONS	2N2483	2N2484	UNIT
		MAX	MAX	
$\overline{NF}$ Average Noise Figure	$V_{CE} = 5 V, I_C = 10 \mu A, R_G = 10 k\Omega, \text{Noise Bandwidth} = 15.7 kHz, \text{See Note 5}$	4	3	dB
NF Spot Noise Figure	$V_{CE} = 5 V, I_C = 10 \mu A, R_G = 10 k\Omega, f = 100 Hz, \text{Noise Bandwidth} = 20 Hz$	15	10	dB
	$V_{CE} = 5 V, I_C = 10 \mu A, R_G = 10 k\Omega, f = 1 kHz, \text{Noise Bandwidth} = 200 Hz$	4	3	dB
	$V_{CE} = 5 V, I_C = 10 \mu A, R_G = 10 k\Omega, f = 10 kHz, \text{Noise Bandwidth} = 2 kHz$	3	2	dB

NOTES: 4. These parameters must be measured using pulse techniques.  $t_p = 300 \mu s$ , duty cycle  $\leq 1\%$ .

5. Average Noise Figure is measured in an amplifier with response down 3 dB at 10 Hz and 10 kHz and a high-frequency rolloff of 6 dB/octave.

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